

Number	Hit#	Search Text	IP	Time Stamp
1	104	hardmask or "hard mask" or SiN or "silicon nitride" same APC or antireflect or "anti reflective coating"	USPAT; EPO; JPO; IBM_TDB	2003/04/14 09:17
2	104	hardmask or "hard mask" or SiN or "silicon nitride" same APC or antireflect or "anti reflective coating" same etch\$3	USPAT; EPO; JPO; IBM_TDB	2003/04/14 09:17
3	116	resist or photoresist or pattern or patterned or patterning same APC or antireflect or "anti reflective coating"	USPAT; EPO; JPO; IBM_TDB	2003/04/14 09:17
4	103	resist or photoresist or pattern or patterned or patterning with APC or antireflect or "anti reflective coating"	USPAT; EPO; JPO; IBM_TDB	2003/04/14 09:17
5	886	resist or photoresist or pattern or patterned or patterning with APC or antireflect or "anti reflective coating" same etch\$3	USPAT; EPO; JPO; IBM_TDB	2003/04/14 10:17
6	192	hardmask or "hard mask" or SiN or "silicon nitride" same resist or photoresist or pattern or patterned or patterning with APC or antireflect or "anti reflective coating" same etch\$3	USPAT; EPO; JPO; IBM_TDB	2003/04/14 09:17
7	127	resist or photoresist or pattern or patterned or patterning with APC or antireflect or "anti reflective coating" same etch\$3 and 488/0.68is.	USPAT; EPO; JPO; IBM_TDB	2003/04/14 09:17
8	1055	hardmask or "hard mask" or SiN or "silicon nitride" with APC or antireflect or "anti reflective coating"	USPAT; EPO; JPO; IBM_TDB	2003/04/14 09:17
9	235	resist or photoresist or pattern or patterned or patterning same hardmask or "hard mask" or SiN or "silicon nitride" with APC or antireflect or "anti reflective coating"	USPAT; EPO; JPO; IBM_TDB	2003/04/14 09:17
10	4672	pattern or patterned or patterning with APC or antireflect or "anti reflective coating"	USPAT; EPO; JPO; IBM_TDB	2003/04/14 09:17
11	481	pattern or patterned or patterning with APC or antireflect or "anti reflective coating" with opening or via or contact	USPAT; EPO; JPO; IBM_TDB	2003/04/14 09:17
12	1269	pattern or patterned or patterning same APC or antireflect or "anti reflective coating" same resist or photoresist	USPAT; EPO; JPO; IBM_TDB	2003/04/14 09:17
13	149	pattern or patterned or patterning with APC or antireflect or "anti reflective coating" with resist or photoresist	USPAT; EPO; JPO; IBM_TDB	2003/04/14 09:17
14	1000	pattern or patterned or patterning with APC or antireflect or "anti reflective coating" with resist or photoresist and 488/0.68is.	USPAT; EPO; JPO; IBM_TDB	2003/04/14 09:17
15	1000	opening or contact same APC or antireflect or "anti reflective coating" same etch\$3	USPAT; EPO; JPO; IBM_TDB	2003/04/14 09:17
16	1000	opening or contact with APC or antireflect or "anti reflective coating" same etch\$3	USPAT; EPO; JPO; IBM_TDB	2003/04/14 09:17
17	1000	opening or contact with APC or antireflect or "anti reflective coating" same etch\$3	USPAT; EPO; JPO; IBM_TDB	2003/04/14 09:17
18	1000	opening or contact with polyimide or	USPAT; EPO; JPO; IBM_TDB	2003/04/14 09:17